

AOS Semiconductor Product Reliability Report

AO3407/AO3407L, rev C

Plastic Encapsulated Device

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This AOS product reliability report summarizes the qualification result for AO3407. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO3407 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AO3407 uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use as a load switch or in PWM applications. Standard Product AO3407 is Pb-free (meets ROHS & Sony 259 specifications). AO3407L is a Green Product ordering option. AO3407 and AO3407L are electrically identical.

Absolute Maximum Ratings T _A =25°C unless otherwise noted						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage		V _{DS}	-30	V		
Gate-Source Voltage		V _{GS}	±20	V		
Continuous Drain	T _A =25°C		-4.1			
Current	T _A =70°C	I _D	-3.5	А		
Pulsed Drain Current		I _{DM}	-20			
	T _A =25°C	Pn	1.4	w		
Power Dissipation	T _A =70°C	I D	1	vv		
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C		

Thermal Characteristics							
Parameter	Symbol	Тур	Max	Units			
Maximum Junction-to- Ambient	T ≤ 10s	D	65	90	°C/W		
Maximum Junction-to- Ambient	Steady- State	- R _{θJA}	85	125	°C/W		
Maximum Junction-to-Lead	Steady- State	R _{θJL}	43	60	°C/W		



II. Die / Package Information:

Process Package Type	AO3407 Standard sub-micron low voltage P channel process 3 leads SOT	AO3407L (Green Compound) Standard sub-micron low voltage P channel process 3 leads SOT
Lead Frame Die Attach Bond wire Mold Material Filler % (Spherical/Flake) Flammability Rating Backside Metallization	Copper with Solder Plate Ag epoxy Au 2mils Epoxy resin with silica filler 90/10 UL-94 V-0 Ti / Ni / Ag	Copper with Solder Plate Ag epoxy Au 2 mils Epoxy resin with silica filler 100/0 UL-94 V-0 Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1*

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO3407 (Standard) & AO3407L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°c Green: 168hr 85°c /85RH +3 cycle reflow@260 °c	Ohr	Standard: 21 lots Green: 7 lots	4235 pcs	0
HTGB	Temp = 150°c , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	4 lots (Note A*)	328 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°c , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	4 lots (Note A*)	328 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°c , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard : 21 lots Green: 6 lots (Note B**)	1485 pcs 50+5 pcs / lot	0
Pressure Pot	121°c , 29.7psi, RH=100%	96 hrs	Standard : 20 lots Green: 5 lots (Note B**)	1375 pcs 50+5 pcs / lot	0
Temperature Cycle	-65°c to 150°c , air to air	250 / 500 cycles	Standard : 18 lots Green: 7 lots (Note B**)	1375 pcs 50+5 pcs / lot	0



III. Result of Reliability Stress for AO3407 (Standard) & AO3407L (Green) Continues

DPA	Internal Vision	NA	5	5	0
	Cross-section		5	5	
	X-ray		5	5	
CSAM		NA	5	5	0
Bond Integrity	Room Temp	0hr	40	40 wires	0
•••	150°c bake	250hr	40	40 wires	
	150°c bake	500hr	40	40 wires	
Solderability	230°c	5 sec	15	15 leads	0
Die shear	150°c	0hr	10	10	0

Note A: The HTGB and HTRB reliability data presents total of available AO3407 and AO3407L burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO3407 and AO3407L comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 10 MTTF = 11449 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO3407). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9 / [2 (N) (H) (Af)]$

= 1.83×10^9 / [2 (164) (168) (258) +2 (2×164) (500) (258) + 2 (164) (1000) (258)] = 10

MTTF = 10^9 / FIT = 1.0×10^8 hrs = 11449 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval **N** = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55° C) Acceleration Factor [**Af**] = **Exp** [Ea / k (1/Tj u - 1/Tj s)]

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Acceleration Factor ratio list:
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	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, 8.617164 X 10^{-5} eV / K



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual. Guaranteed Outgoing Defect Rate: **< 25 ppm** Quality Sample Plan: conform to **Mil-Std-105D**